Product data sheet

1. General description

NPN low V_{CEsat} transistor in a medium power flat lead SOT89 plastic package.

PNP complement: PBSS5320X

2. Features and benefits

- SOT89 (SC-62) package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- · Higher efficiency leading to less heat generation
- · Reduced printed-circuit board requirements.
- AEC-Q101 qualified

3. Applications

- · Power management
 - · DC/DC converters
 - · Supply line switching
 - Battery charger
 - · LCD backlighting.
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs).
 - Inductive load driver (e.g. relays, buzzers and motors).

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	20	V
I _C	collector current		[1]	-	-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	5	Α
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 0.1 A		220	-	-	
R _{CEsat}	collector-emitter saturation resistance	I _C = 3 A; I _B = 300 mA	[2]	-	85	105	mΩ

^[1] Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated.



^[2] Pulsed test: $t_p \le 300 \,\mu s$; $\delta \le 0.02$

20 V, 3 A NPN low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		
3	В	base		B — (
			3 2 1	E
			SOT89	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4320X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4320X	S44

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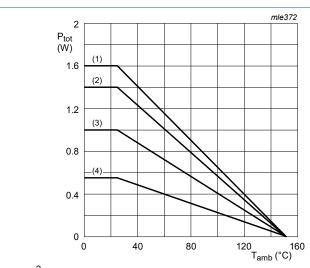
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	20	V
V_{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current		[1]	-	3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	5	А
I _B	base current			-	0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	550	mW
			[3]	-	1	W
			[4]	-	1.4	W
			[5]	-	1.6	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm² [3]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on a ceramic PCB 7 cm², single-sided copper, tin-plated.



- (1) Ceramic PCB; 7 cm² mounting pad for collector (2) FR4 PCB; 6 cm² copper mounting pad for collector (3) FR4 PCB; 1 cm² copper mounting pad for collector
- (4) Standard footprint

Power derating curves Fig. 1.

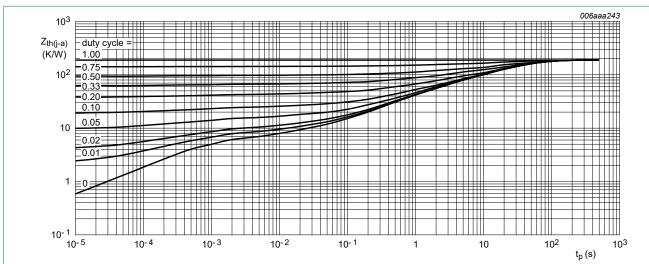
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9. Thermal characteristics

Table 6. Thermal characteristics

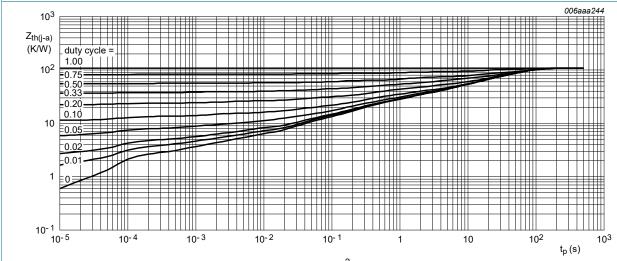
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air [1] [2]	[1]	-	-	225	K/W
			[2]	-	-	125	K/W
			[3]	-	-	90	K/W
			[4]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on a ceramic PCB 7 cm², single-sided copper, tin-plated. [3]
- [4]



Mounted on FR4 PCB; standard footprint.

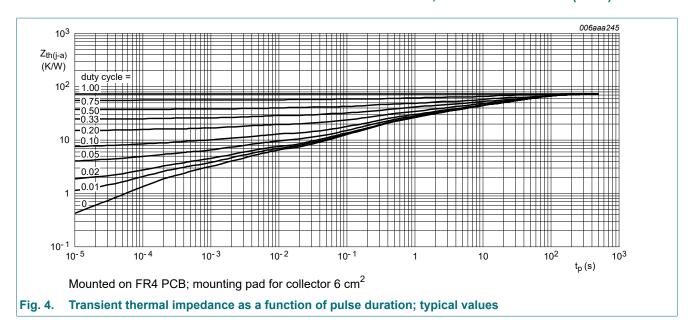
Transient thermal impedance as a function of pulse duration; typical values Fig. 2.



Mounted on FR4 PCB; mounting pad for collector 1 cm²

Transient thermal impedance as a function of pulse duration; typical values

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10. Characteristics

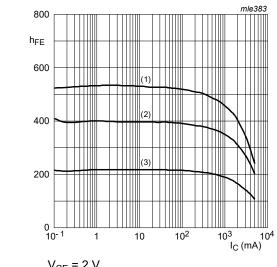
Table 7. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A		-	-	100	nA
	current	V _{CB} = 20 V; I _E = 0 A; T _j = 150 °C		-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 20 V; V _{BE} = 0 V		-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 0.1 A		220	-	-	
		V _{CE} = 2 V; I _C = 0.5 A		220	-	-	
		V _{CE} = 2 V; I _C = 1 A	[1]	220	-	-	
		V _{CE} = 2 V; I _C = 2 A	[1]	200	-	-	
		V _{CE} = 2 V; I _C = 3 A	[1]	150	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 0.5 A; I _B = 50 mA		-	-	70	mV
		I _C = 1 A; I _B = 50 mA		-	-	120	mV
		I _C = 2 A; I _B = 100 mA		-	-	240	mV
		I _C = 3 A; I _B = 300 mA	[1]	-	-	310	mV
R _{CEsat}	collector-emitter saturation resistance		[1]	-	85	105	mΩ
V _{BEsat}	base-emitter saturation	I _C = 2 A; I _B = 100 mA		-	-	1.1	V
	voltage	I _C = 3 A; I _B = 300 mA	[1]	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 1 A		1.1	-	-	V
f _T	transition frequency	V _{CE} = 5 V; I _C = 100 mA; f = 100 MHz		100	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}$		-	-	35	pF

[1] Pulsed test: $t_p \le 300 \,\mu s$; $\delta \le 0.02$

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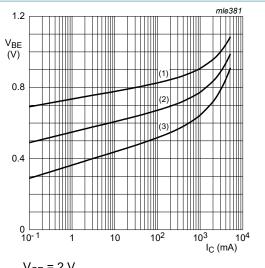
$$V_{CE} = 2 V$$

(2)
$$T_{amb} = 25 \,^{\circ}\text{C}$$

(3) $T_{amb} = -55 \,^{\circ}\text{C}$

$$(3) T_{amb} = -55 °C$$

Fig. 5. DC current gain as a function of collector current; typical values



$$V_{CE} = 2 V$$

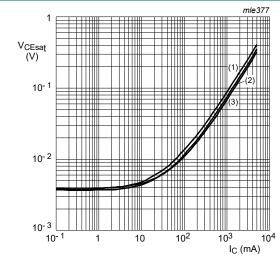
$$V_{CE} = 2 V$$

(1) $T_{amb} = -55 °C$
(2) $T_{amb} = 25 °C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



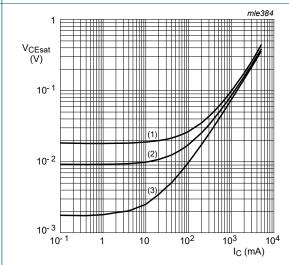
$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \,^{\circ}C$$

Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values



$$I_{amb} = 25 \, ^{\circ}C$$

$$T_{amb} = 25 \, ^{\circ}C$$

(1) $I_{C}/I_{B} = 100$

(2)
$$I_{\rm C}/I_{\rm B} = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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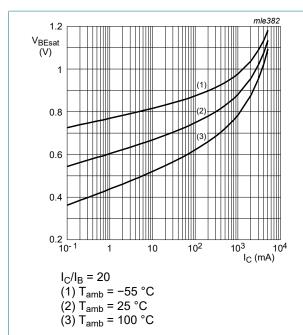
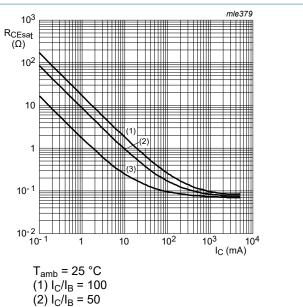
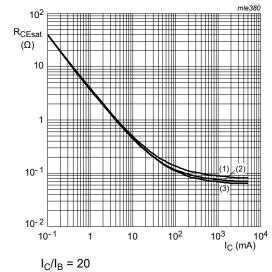


Fig. 9. collector current; typical values



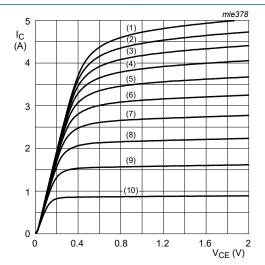
(2) $I_C/I_B = 50$ (3) $I_C/I_B = 10$

Base-emitter saturation voltage as a function of Fig. 10. Equivalent on-resistance as a function of collector current; typical values



(1) $T_{amb} = 100 \, ^{\circ}C$ (2) T_{amb} = 25 °C (3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 11. Equivalent on-resistance as a function of collector current; typical values



T_{amb} = 25 °C (1) $I_B = 25 \text{ mA}$ (2) $I_B = 22.5 \text{ mA}$ (3) $I_B = 20 \text{ mA}$ $(4) I_B = 17.5 \text{ mA}$ $(5) I_B = 15 mA$ (6) $I_B = 12.5 \text{ mA}$ $(7) I_B = 10 mA$

(8) $I_B = 7.5 \text{ mA}$ (9) $I_B = 5 \text{ mA}$ $(10) I_B = 2.5 mA$

Fig. 12. Collector current as a function of collectoremitter voltage; typical values

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11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

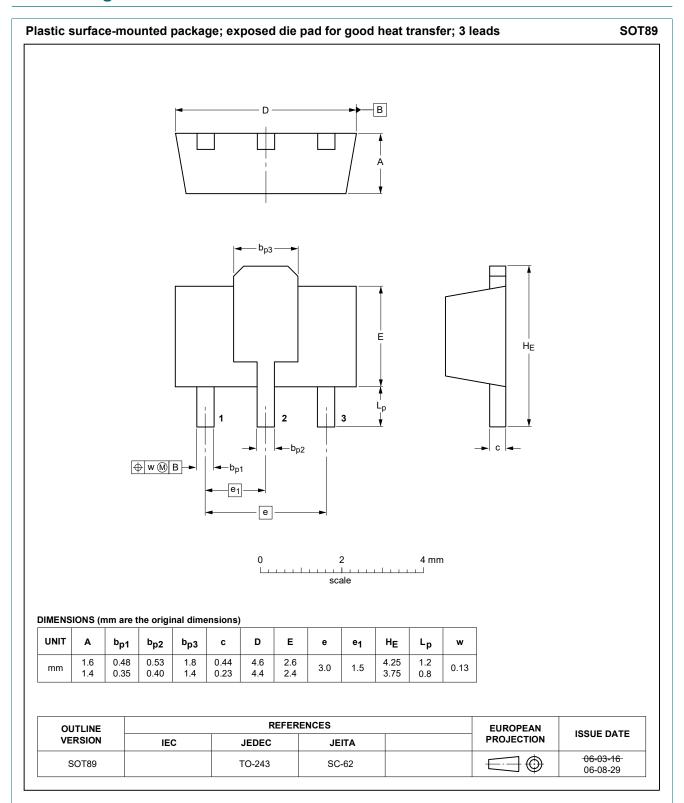
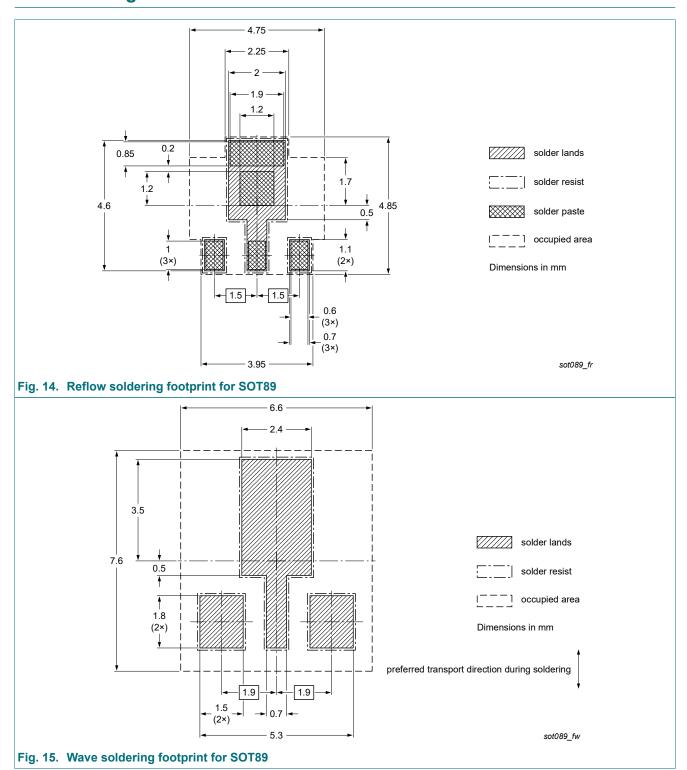


Fig. 13. Package outline SOT89

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4320X v.1	20190527	Product data sheet	-	PBSS4320X v.2		
Modifications:	 Characteristics: V_{BEsat} corrected from typical to maximum. The format of this data sheet has been redesigned to comply with the identity guidelines Nexperia. Legal texts have been adapted to the new company name where appropriate. 					
PBSS4320X v.2	20041103	Product data sheet	-	PBSS4320X v.1		
PBSS4320X v.1	20031215	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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